

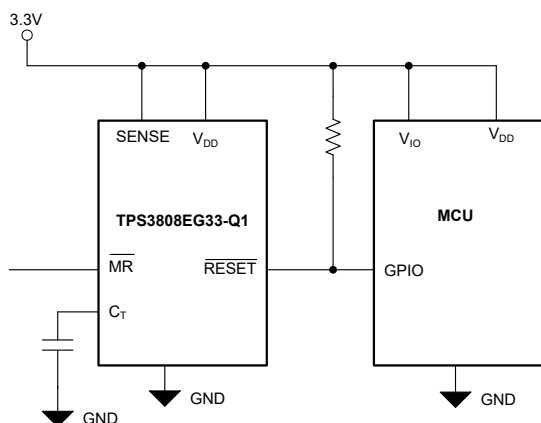
TPS3808E-Q1 低静止電流、遅延時間プログラム可能、車載用、監視回路

1 特長

- 以下の結果で AEC-Q100 認定済み:
 - デバイス温度グレード 1: -40°C ~ +125°C
- 電源レールの低電圧監視
 - 高いスレッシュホールド精度 (標準値 1%) による信頼性の高い監視
 - 0.9V ~ 5V の固定電圧スレッシュホールド オプション
 - 可変電圧オプションを利用可能 (0.405V)
 - 独立した監視用の Sense ピンと電力用の V_{DD} ピン
- 超低消費電力の小型ソリューション
 - 静止電流 0.6μA (標準値)
 - コンパクトな 6 ピン SOT23 パッケージ (2.9mm × 1.6mm)
- 高度な構成が可能なリセット時間遅延によって安全でない電源オンを防止
 - 1.25ms ~ 10s で調整可能
- 独立したマニュアルリセット入力 (MR) によって RESET 出力を必要に応じてアサート

2 アプリケーション

- ADAS ドメイン・コントローラ
- 車載ゲートウェイ
- 車載ヘッド・ユニット
- デジタル・コックピット処理装置
- テレマティクス制御ユニット
- ドライバー監視



代表的なアプリケーション

3 概要

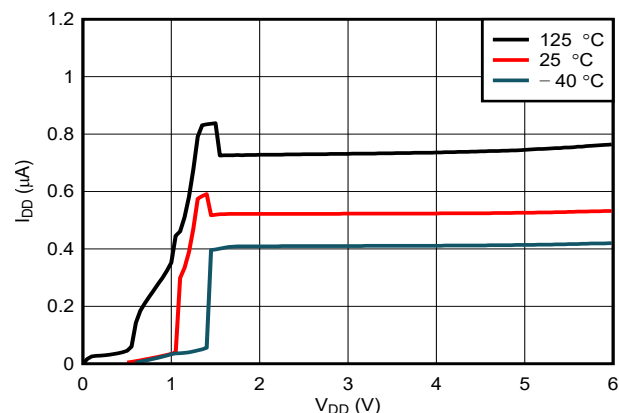
TPS3808E-Q1 ファミリーはマイクロプロセッサ監視回路で、0.4V ~ 5V のシステム電圧を監視でき、SENSE 電圧が設定済みのスレッシュホールドより低下したとき、またはマニュアルリセット (MR) ピンが論理 LOW に低下したとき、オープンドレインの RESETE 信号をアサートします。RESETE 出力は、SENSE 電圧とマニュアル・リセット (MR) がそれぞれのスレッシュホールド以上に復帰した後も、ユーザーが設定した遅延時間だけ LOW に維持されます。

TPS3808E-Q1 デバイスは、高精度の基準電圧を使用して、0.5% のスレッシュホールド精度を実現しています。リセット遅延時間は、C_T ピンを未接続にすることで 20ms に設定でき、抵抗を使用して C_T ピンを V_{DD} に接続することで 300ms に設定できます。または、C_T ピンを外部コンデンサに接続することで 1.25ms ~ 10s の範囲でユーザー調整することもできます。TPS3808E デバイスは、静止電流が 0.6μA (代表値) と非常に小さいため、バッテリー駆動のアプリケーションに適しています。TPS3808E-Q1 は SOT-23-6 で供給され、-40°C ~ 125°C (T_J) の温度範囲で完全に動作が規定されています。

デバイス情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
TPS3808E	SOT-23 (6)	2.90mm × 1.60mm

- (1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。



消費電流と電源電圧との関係



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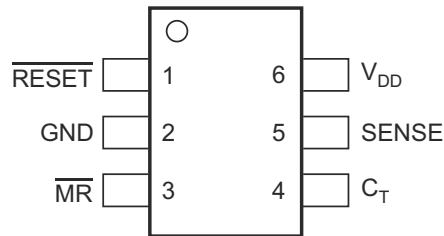
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4 Device Voltage Thresholds

The following table shows the nominal rail to be monitored and the corresponding threshold voltage of the device.

PART NUMBER	NOMINAL SUPPLY VOLTAGE	THRESHOLD VOLTAGE (V _{IT})
TPS3808EG01	Adjustable	0.405 V
TPS3808EG09	0.9 V	0.84 V
TPS3808EG12	1.2 V	1.12 V
TPS3808EG125	1.25 V	1.16 V
TPS3808EG15	1.5 V	1.40 V
TPS3808EG18	1.8 V	1.67 V
TPS3808EG19	1.9 V	1.77 V
TPS3808EG25	2.5 V	2.33 V
TPS3808EG30	3 V	2.79 V
TPS3808EG33	3.3 V	3.07 V
TPS3808EG50	5 V	4.65 V

5 Pin Configuration and Functions



**図 5-1. DBV Package
6-Pin SOT-23
Top View**

表 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	SOT-23		
C_T	4	I	Reset period programming pin. Connecting this pin to V_{DD} through a 40-k Ω to 200-k Ω resistor or leaving it open results in fixed delay times. Connecting this pin to a ground referenced capacitor ≥ 130 pF gives a user-programmable delay time.
GND	2	—	Ground
\overline{MR}	3	I	Driving the manual reset pin (\overline{MR}) low asserts \overline{RESET} . \overline{MR} is internally tied to V_{DD} by a 90-k Ω pull-up resistor.
\overline{RESET}	1	O	\overline{RESET} is an open-drain output that is driven to a low-impedance state when \overline{RESET} is asserted (either the SENSE input is lower than the threshold voltage (V_{IT}) or the \overline{MR} pin is set to a logic low). \overline{RESET} remains low (asserted) for the reset period after both SENSE is above V_{IT} and \overline{MR} is set to a logic high. A pull-up resistor from 10 k Ω to 1 M Ω must be used on this pin, this allows the reset pin to attain voltages higher than V_{DD} .
SENSE	5	I	This pin is connected to the voltage to be monitored. If the voltage at this terminal drops below the threshold voltage V_{IT} , then \overline{RESET} is asserted.
V_{DD}	6	I	Supply voltage. For good analog design, place a 0.1- μ F ceramic capacitor close to this pin.

6 Specification

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Voltage	V_{DD} , V_{CT} , V_{RESET} , V_{MR} , V_{SENSE}	-0.3	6.5	V
Current	I_{RESET}		±5	mA
Temperature ⁽²⁾	Operating junction temperature, T_J	-40	150	°C
	Operating free-air temperature, T_A	-40	150	°C
	Storage temperature, T_{stg}	-65	150	°C

- (1) Stresses beyond values listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) As a result of the low dissipated power in this device, it is assumed that $T_J = T_A$.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V
		Charged device model (CDM), per AEC Q100-011	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V_{DD}	Supply pin voltage	1.7		6	V
V_{SENSE}	Input pin voltage	0		6	V
V_{CT}	CT pin voltage			V_{DD}	V
V_{MR}	\overline{MR} pin Voltage	0		6	V
V_{RESET}	Output pin voltage	0		6	V
I_{RESET}	Output pin current	0		5	mA
T_J	Junction temperature (free-air temperature)	-40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS3808E-Q1	UNIT
		DBV (SOT23-6)	
		6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	131.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	91.7	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	67.6	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	91.3	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

At $1.7\text{ V} \leq V_{DD} \leq 6\text{ V}$, CT = MR = Open, RESET Voltage (V_{RESET}) = 100 k Ω to V_{DD} , RESET load = 50 pF, and over the operating free-air temperature range of -40°C to 125°C , unless otherwise noted. Typical values are at $T_J = 25^{\circ}\text{C}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{DD}	Supply Voltage		1.7		6	V
V_{DD}	Supply Voltage	0C to 85C	1.65		6	V
V_{POR}	Power on reset voltage ⁽²⁾	$V_{OL(max)} = 0.25\text{ V}$, $I_{OUT} = 15\text{ }\mu\text{A}$			1	V
$V_{IT-(UV)}$	Negative-going threshold accuracy	Fixed threshold TPS3808EG01	-2	± 1	2	%
$V_{IT-(UV)}$	Negative-going threshold accuracy		-1.5	± 0.5	1.5	%
$V_{IT-(UV)}$	Negative-going threshold accuracy	-40C to 85C	-1.25	± 0.5	1.25	%
V_{HYS}	Hysteresis Voltage ⁽¹⁾	Fixed Vth		1	2.5	%
V_{HYS}	Hysteresis Voltage ⁽¹⁾	Adjustable Vth		1	2.5	%
V_{HYS}	Hysteresis Voltage ⁽¹⁾	-40C to 85C		1	2	%
I_{DD}	Supply current	$V_{DD} = 3.3\text{ V}$		0.6	1.5	μA
I_{DD}	Supply current	$V_{DD} = 6\text{ V}$		0.6	1.5	μA
I_{SENSE}	Input current, SENSE pin	$V_{SENSE} = V_{IT}$, TPS3808EG01	-25		25	nA
I_{SENSE}	Input current, SENSE pin	$V_{SENSE} = 6\text{ V}$, Fixed Versions		0.75	1.25	μA
V_{OL}	Low level output voltage	$1.3\text{ V} \leq V_{DD} < 1.7\text{ V}$, $I_{OUT} = 0.4\text{ mA}$			300	mV
V_{OL}	Low level output voltage	$1.7\text{ V} \leq V_{DD} < 6\text{ V}$, $I_{OUT} = 1\text{ mA}$			400	mV
I_{LKG}	Open drain output leakage current	$V_{DD} = V_{RESET} = 6\text{ V}$			300	nA
V_{MR_L}	MR logic low input				$0.3 V_{DD}$	V
V_{MR_H}	MR logic high input		$0.7 V_{DD}$			V
R_{MR}	Manual reset Internal pullup resistance			90		K Ω

(1) Hysteresis is with respect of the tripoint $V_{IT-(UV)}$.

(2) V_{POR} is the minimum V_{DD} voltage level for a controlled output state.

6.6 Timing Requirements

At $1.7\text{ V} \leq V_{DD} \leq 6\text{ V}$, $CT = MR = \text{Open}$, $\overline{\text{RESET}}$ Voltage ($V_{\overline{\text{RESET}}}$) = $100\text{ k}\Omega$ to V_{DD} , $\overline{\text{RESET}}$ load = 50 pF , and over the operating free-air temperature range of -40°C to 125°C , unless otherwise noted. Typical values are at $T_J = 25^\circ\text{C}$.

			MIN	NOM	MAX	UNIT
t_D	Reset time delay	$CT = \text{Open}$	12	20	28	ms
t_D	Reset time delay	$CT = V_{DD}$	180	300	420	ms
t_D	Reset time delay	$CT = 130\text{ pF}$	0.75	1.25	1.75	ms
t_D	Reset time delay	$CT = 150\text{ nF}$		0.83		s
t_{PD}	Propagation detect delay ^{(1) (2)}			30	50	μs
t_{SD}	Startup delay ⁽³⁾			300		μs
$t_{GI} (V_{IT-})$	Glitch Immunity undervoltage $V_{IT-(UV)}$, 5% Overdrive ⁽¹⁾			5		μs
$t_{GI} (MR)$	Glitch Immunity \overline{MR} pin			50		ns
$t_{PD} (MR)$	Propagation delay from \overline{MR} low to assert $\overline{\text{RESET}}$			500		ns

- (1) 5% Overdrive from threshold. Overdrive % = $[V_{\text{SENSE}} - V_{IT}] / V_{IT}$; Where V_{IT} stands for $V_{IT-(UV)}$
- (2) t_{PD} measured from threshold trip point ($V_{IT-(UV)}$ or $V_{IT+(OV)}$) to $\overline{\text{RESET}} V_{OL}$ voltage
- (3) During the power-on sequence, V_{DD} must be at or above $V_{DD(MIN)}$ for at least $t_{SD} + t_D$ before the output is in the correct state.

6.7 Timing Diagram

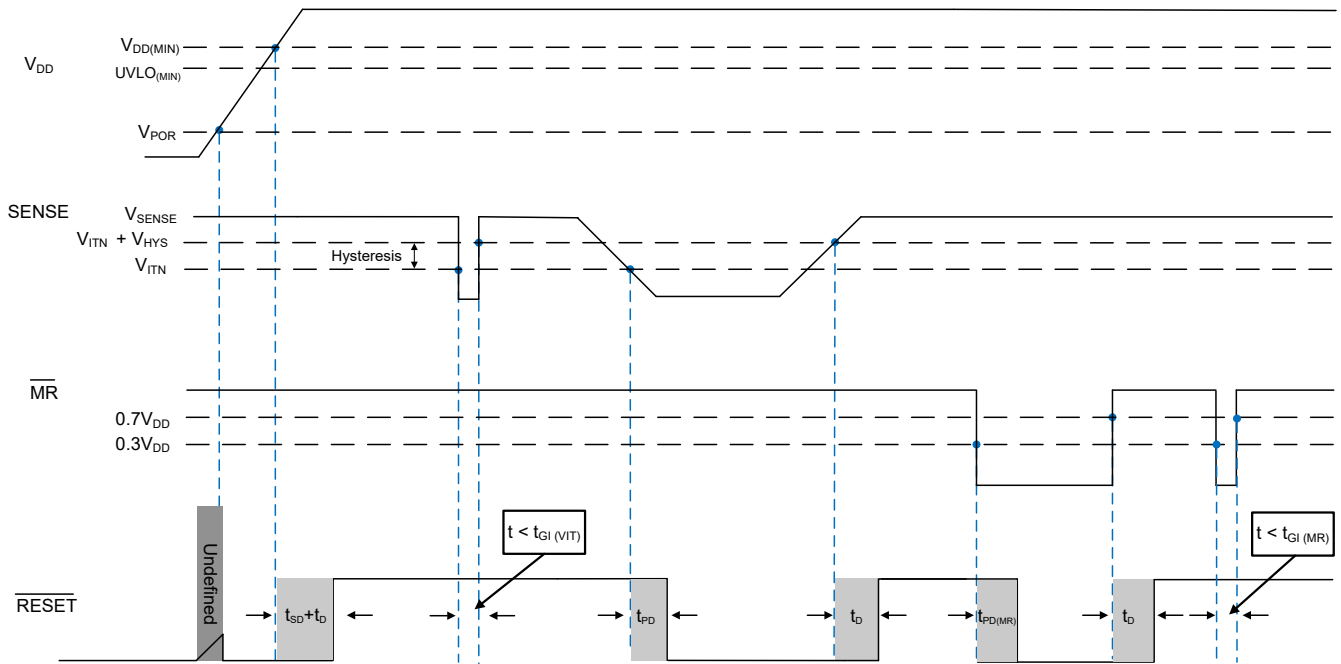
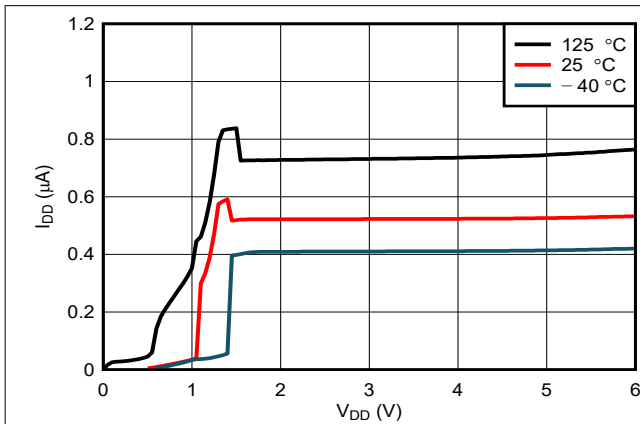


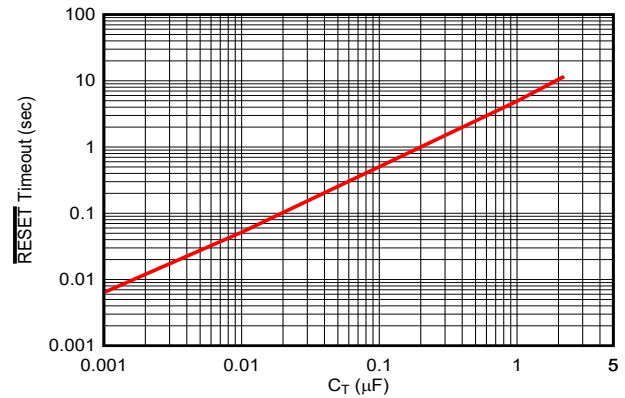
図 6-1. Timing Diagram

7 Typical Characteristics

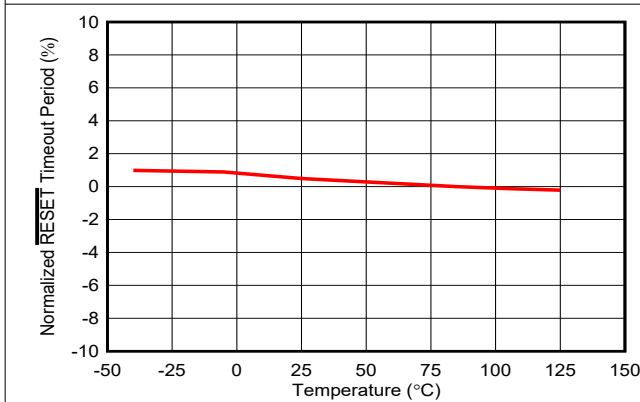
At $T_J = 25^\circ\text{C}$, $V_{DD} = 3.3\text{ V}$, $R_{LRESET} = 100\text{ k}\Omega$, and $C_{LRESET} = 50\text{ pF}$, unless otherwise noted.



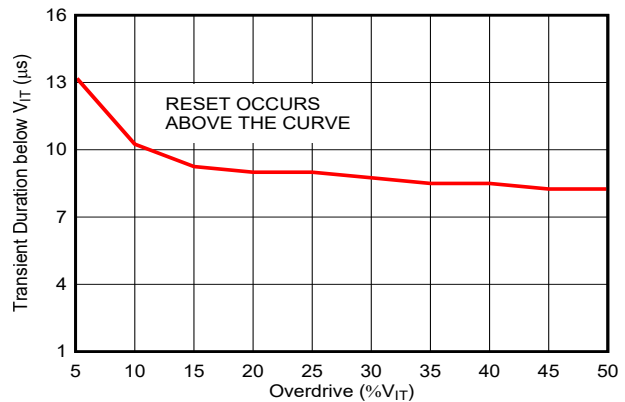
7-1. Supply Current vs Supply Voltage



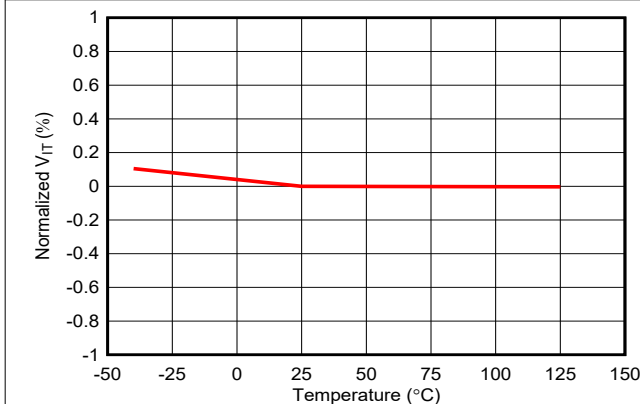
7-2. RESET Time-Out Period vs C_T



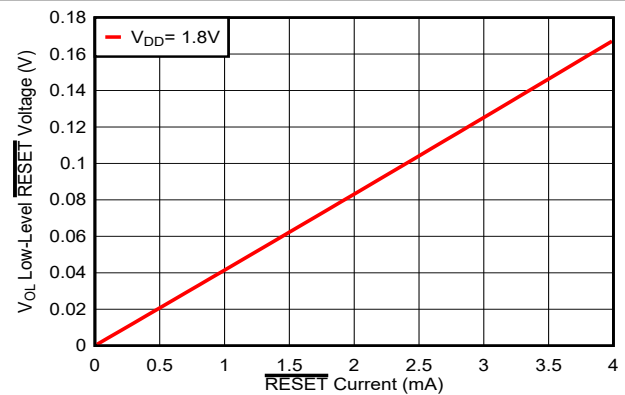
7-3. Normalized RESET Time-Out Period vs Temperature ($C_T = \text{Open}$, $C_T = V_{DD}$, $C_T = \text{Any}$)



7-4. Maximum Transient Duration at Sense vs Sense Threshold Overdrive Voltage



7-5. Normalized Sense Threshold Voltage (V_{IT}) vs Temperature



7-6. Low-Level RESET Voltage vs RESET Current

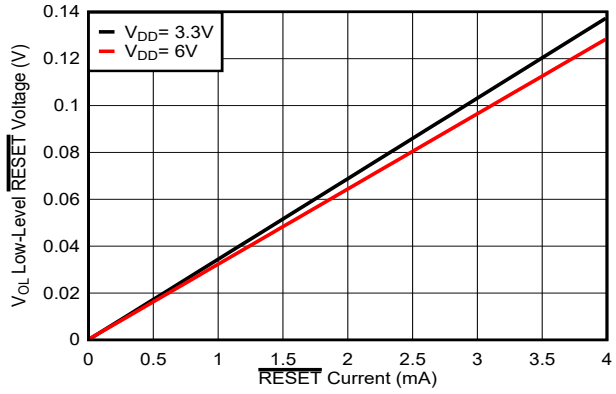


図 7-7. Low-Level RESET Voltage vs RESET Current

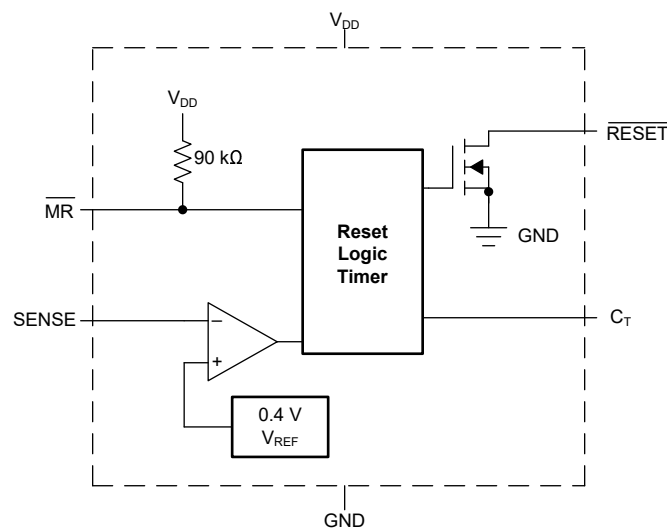
8 Detailed Description

8.1 Overview

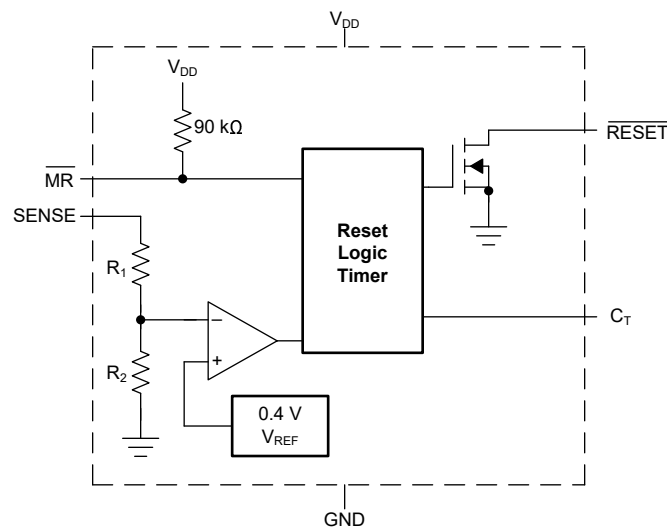
The TPS3808E microprocessor supervisory product family is a low quiescent current single channel supervisor which has programmable delay time and manual reset features. The TPS3808E-Q1 microprocessor supervisory product family is designed to assert a $\overline{\text{RESET}}$ signal when either the SENSE pin voltage drops below V_{IT} or the manual reset ($\overline{\text{MR}}$) is driven low. The $\overline{\text{RESET}}$ output remains asserted for a user-adjustable time after both the manual reset ($\overline{\text{MR}}$) and SENSE voltages return above their respective thresholds.

TPS3808E product family comes with fixed threshold options, which eliminates the need of external resistor divider and can monitor the standard voltage rails from 0.9 V to 5 V, and adjustable threshold option, which can monitor down to 0.4 V with both high threshold accuracy. By connecting an external resistor divider, the adjustable version also can also monitor standard voltage rails.

8.2 Functional Block Diagram



Adjustable-Voltage Version



Fixed-Voltage Version

8.3 Feature Description

A broad range of voltage threshold and reset delay time adjustments are available for the TPS3808E-Q1 device, allowing these devices to be used in a wide array of applications. Reset threshold voltages can be factory-set from 0.82 V to 3.3 V or from 4.4 V to 5 V, while the adjustable variant can be set to any voltage above 0.405 V using an external resistor divider. Two preset delay times are also user-selectable: connecting the C_T pin to V_{DD} results in a 300-ms reset delay, whereas leaving the C_T pin open yields a 20-ms reset delay. In addition, connecting a capacitor between C_T and GND allows the designer to select any reset delay period from 1.25 ms to 10 s.

8.3.1 SENSE Input

The SENSE input provides a pin at which any system voltage can be monitored. If the voltage on this pin drops below V_{IT} , then $\overline{\text{RESET}}$ is asserted. The comparator has a built-in hysteresis to make sure there are smooth $\overline{\text{RESET}}$ assertions and de-assertions. It is good analog design practice to put a 1-nF bypass capacitor on the SENSE input to reduce sensitivity to transients and layout parasitics.

The TPS3808E-Q1 device is relatively immune to short negative transients on the SENSE pin. Sensitivity to transients is dependent on threshold overdrive.

The adjustable variant can be used to monitor any voltage rail down to 0.405 V using the circuit shown in [Figure 8-1](#).

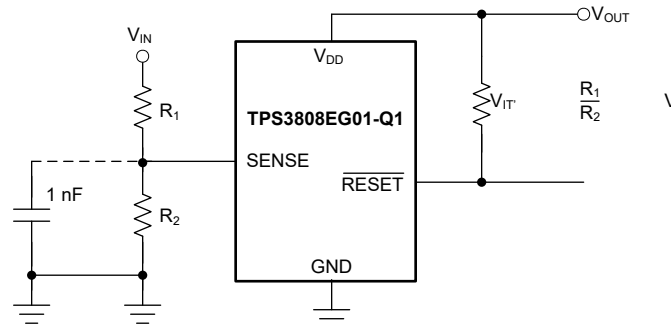


Figure 8-1. Using the TPS3808EG01-Q1 to Monitor a User-Defined Threshold Voltage

8.3.2 Selecting the RESET Delay Time

The TPS3808E-Q1 has three options for setting the $\overline{\text{RESET}}$ delay time as shown in [Figure 8-2](#). [Figure 8-2](#) (a) shows the configuration for a fixed 300-ms typical delay time by tying C_T to V_{DD} ; a resistor from 40 k Ω to 200 k Ω must be used. Supply current is not affected by the choice of resistor. [Figure 8-2](#) (b) shows a fixed 20-ms delay time by leaving the C_T pin open. [Figure 8-2](#) (c) shows a ground referenced capacitor connected to C_T for a user-defined program time between 1.25 ms and 10 s.

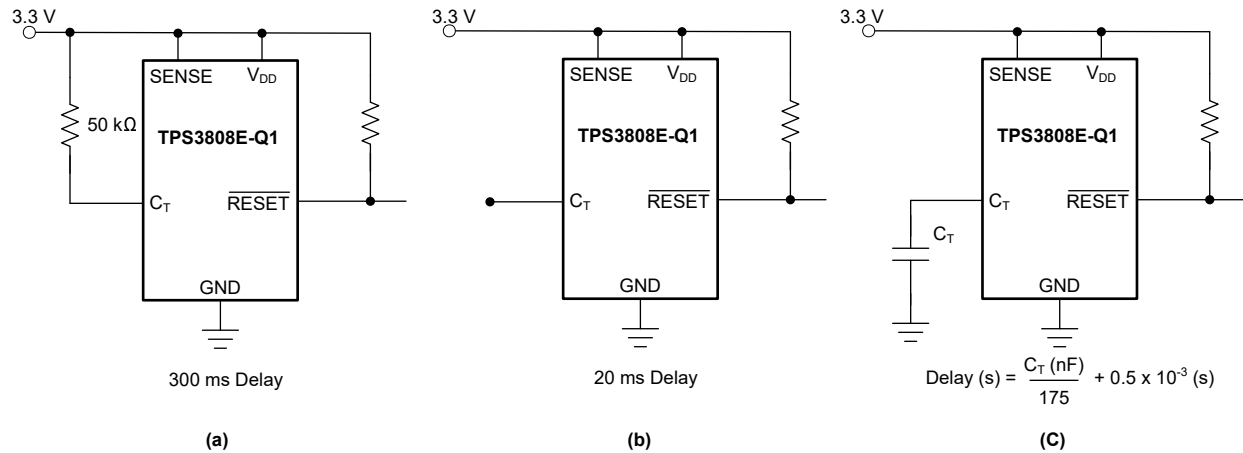


图 8-2. Configuration Used to Set the $\overline{\text{RESET}}$ Delay Time

The capacitor C_T should be ≥ 100 pF nominal value in order for the TPS3808Exxx to recognize that the capacitor is present. The capacitor value for a given delay time can be calculated using 式 1.

$$C_T \text{ (nF)} = [t_D \text{ (s)} - 0.5 \times 10^{-3} \text{ (s)}] \times 175 \quad (1)$$

The reset delay time is determined by the time it takes an on-chip precision 220-nA current source to charge the external capacitor to the internal threshold. When a $\overline{\text{RESET}}$ is asserted, the capacitor is discharged. When the $\overline{\text{RESET}}$ conditions are cleared, the internal current source is enabled and begins to charge the external capacitor. When the voltage on this capacitor reaches higher than the internal threshold, $\overline{\text{RESET}}$ is deasserted. Note that a low-leakage type capacitor such as a ceramic should be used, and that stray capacitance around this pin may cause errors in the reset delay time.

8.3.3 Manual RESET ($\overline{\text{MR}}$) Input

The manual reset ($\overline{\text{MR}}$) input allows a processor or other logic circuits to initiate a reset. A logic low ($0.3 V_{DD}$) on $\overline{\text{MR}}$ causes $\overline{\text{RESET}}$ to assert. After $\overline{\text{MR}}$ returns to a logic high and SENSE is above the reset threshold, $\overline{\text{RESET}}$ is de-asserted after the user-defined reset delay expires. Note that $\overline{\text{MR}}$ is internally tied to V_{DD} using a 90-k Ω resistor, so this pin can be left unconnected if $\overline{\text{MR}}$ is not used.

See 图 8-3 for how $\overline{\text{MR}}$ can be used to monitor multiple system voltages. Note that if the logic signal driving $\overline{\text{MR}}$ does not go fully to V_{DD} , there is some additional current draw into V_{DD} as a result of the internal pullup resistor on $\overline{\text{MR}}$. To minimize current draw, a logic-level FET can be used as illustrated in 图 8-4.

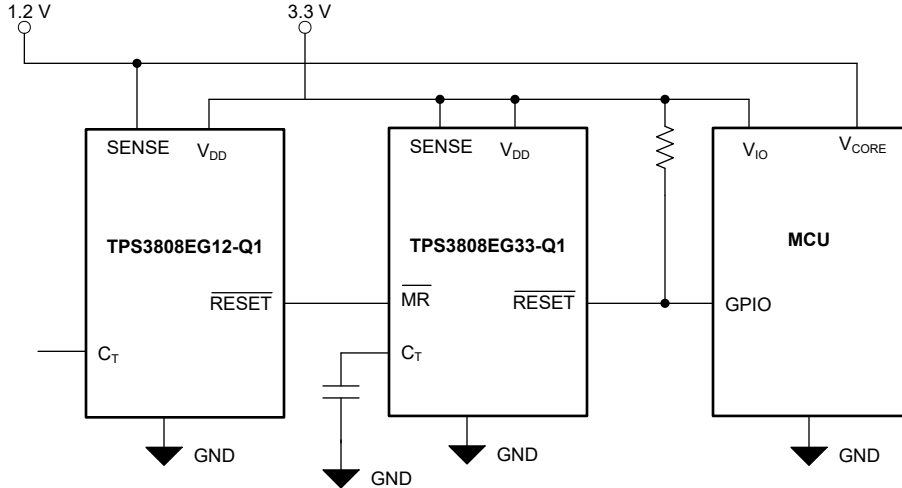


図 8-3. Using \overline{MR} to Monitor Multiple System Voltages

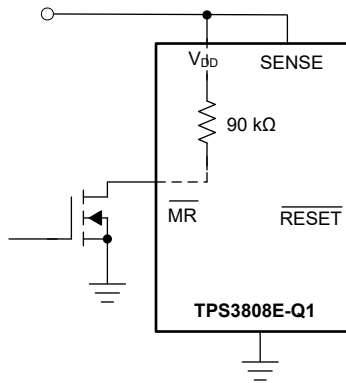


図 8-4. Using an External MOSFET to Minimize I_{DD} When \overline{MR} Signal Does Not Go to V_{DD}

8.3.4 RESET Output

\overline{RESET} remains high (unasserted) as long as SENSE is above its threshold (V_{IT}) and the manual reset (\overline{MR}) is logic high. If either SENSE falls below V_{IT} or \overline{MR} is driven low, \overline{RESET} is asserted, driving the \overline{RESET} pin to a low impedance.

Once \overline{MR} is again logic high and SENSE is above $V_{IT} + V_{HYS}$ (the threshold hysteresis), a delay circuit is enabled that holds \overline{RESET} low for a specified reset delay period. Once the reset delay has expired, the \overline{RESET} pin goes to a high impedance state. The pullup resistor from the open-drain \overline{RESET} to the supply line can be used to allow the reset signal for the microprocessor to have a voltage higher than V_{DD} (up to 6 V). The pullup resistor should be no smaller than 10 k Ω as a result of the finite impedance of the \overline{RESET} line.

8.4 Device Functional Modes

表 8-1. Truth Table

\overline{MR}	SENSE > V_{IT}	RESET
L	0	L
L	1	L
H	0	L
H	1	H

8.4.1 Normal Operation ($V_{DD} > V_{DD(min)}$)

When V_{DD} is greater than $V_{DD(min)}$, the \overline{RESET} signal is determined by the voltage on the SENSE pin and the logic state of \overline{MR} .

- \overline{MR} high: When the voltage on V_{DD} is greater than 1.7 V for a time of the selected t_D , the \overline{RESET} signal corresponds to the voltage on SENSE relative to V_{IT} .
- \overline{MR} low: in this mode, \overline{RESET} is held low regardless of the value of the SENSE pin.

8.4.2 Above Power-On Reset but Less Than $V_{DD(min)}$ ($V_{POR} < V_{DD} < V_{DD(min)}$)

When the voltage on V_{DD} is less than the device $V_{DD(min)}$ voltage, and greater than the power-on reset voltage (V_{POR}), the \overline{RESET} signal is asserted and low impedance, respectively, regardless of the voltage on the SENSE pin.

8.4.3 Below Power-On Reset ($V_{DD} < V_{POR}$)

When the voltage on V_{DD} is lower than the required voltage (V_{POR}) needed to internally pull the asserted output to GND, \overline{RESET} is undefined and should not be relied upon for proper device function.

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The following sections describe in detail how to properly use this device, depending on the requirements of the final application.

9.2 Typical Application

A typical application of the TPS3808E-Q1 used with a 3.3-V processor is shown in [Figure 9-1](#). The open-drain RESET output is typically connected to the RESET input of a microprocessor. A pullup resistor must be used to hold this line high when RESET is not asserted. The RESET output is undefined for voltage below 0.8 V, but this characteristic is normally not a problem because most microprocessors do not function below this voltage.

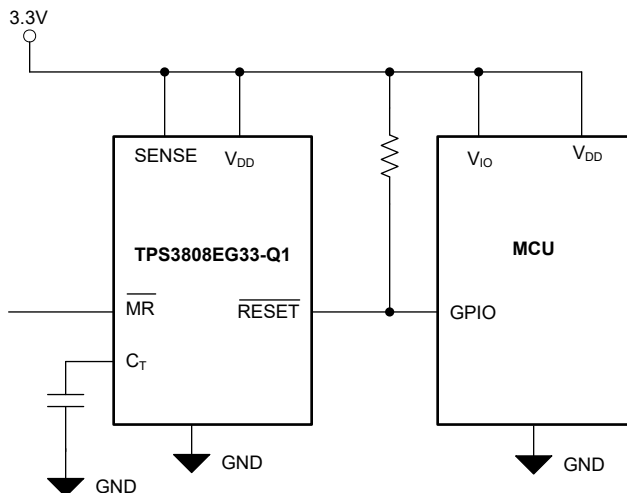


Figure 9-1. Typical Application of the TPS3808E-Q1 With a C2000 Processor

9.2.1 Design Requirements

The TPS3808E-Q1 is intended to drive the RESET input of a microprocessor. The RESET pin is pulled high with a 100-kΩ resistor and the reset delay time is controlled by C_T depending on the reset requirement times of the microprocessor. In this case, C_T is left open for a typical reset delay time of 20 ms.

9.2.2 Detailed Design Procedure

The primary constraint for this application is the reset delay time. In this case, because C_T is open, it is set to 20 ms. A 0.1-μF decoupling capacitor is connected to the V_{DD} pin and a 100-kΩ resistor is used to pull up the RESET pin high. The MR pin can be connected to an external signal if desired.

9.2.2.1 Immunity to SENSE Pin Voltage Transients

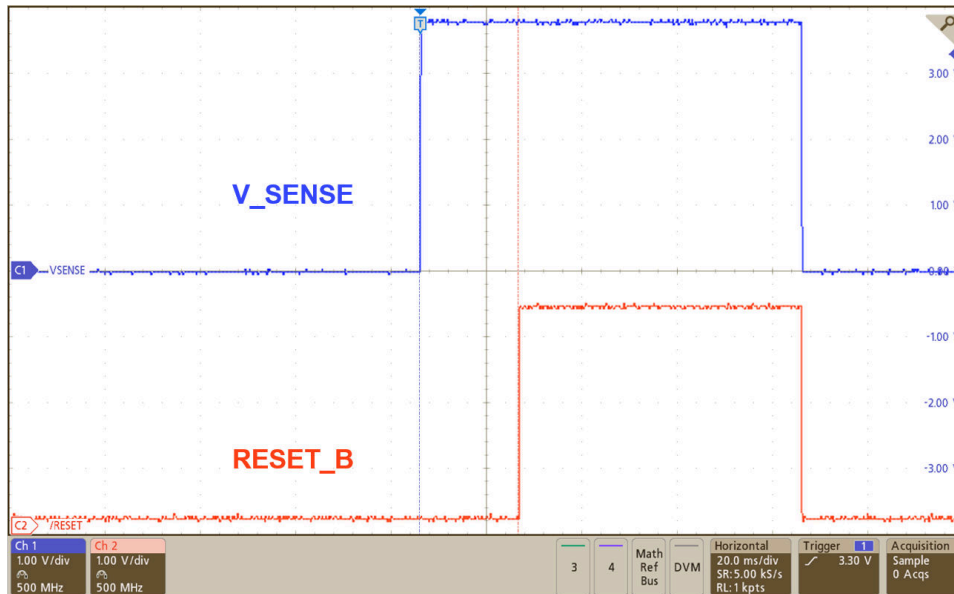
The TPS3808E-Q1 is relatively immune to short negative transients on the SENSE pin. Sensitivity to transients depends on threshold overdrive. Threshold overdrive is defined by how much the V_{SENSE} exceeds the specified threshold, and is important to know because the smaller the overdrive, the slower the RESET response. Threshold overdrive is calculated as a percent of the threshold in question, as shown in 式 2:

$$\text{Overdrive} = | (V_{SENSE} / V_{IT} - 1) \times 100\% | \tag{2}$$

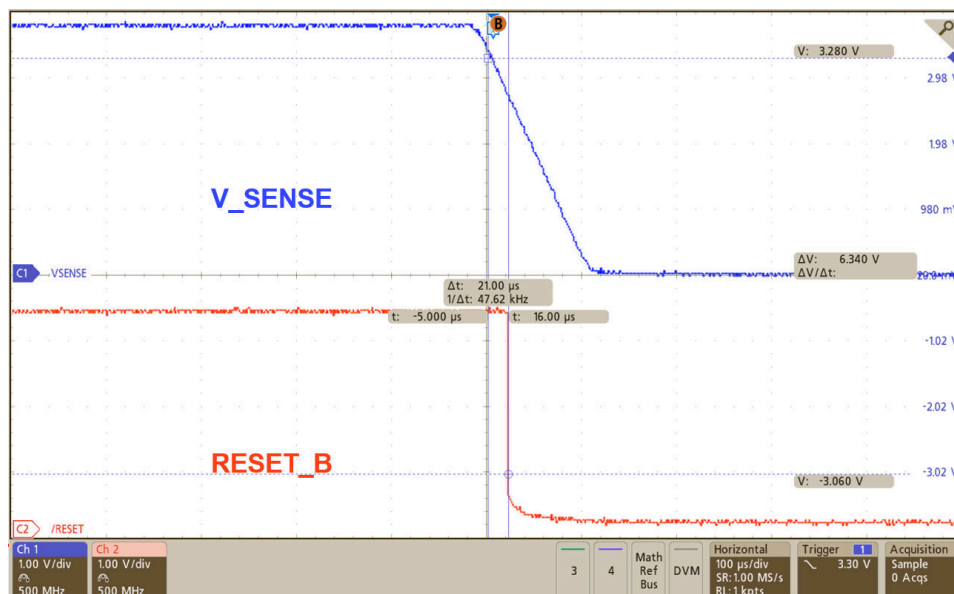
where:

- V_{IT} is the threshold voltage.

9.2.3 Application Curve



9-2. Reset Time Delay



9-3. Propagation Detect Delay

9.3 Power Supply Recommendations

These devices are designed to operate from an input supply with a voltage range between 1.7 V and 6. V. Use a low-impedance power supply to eliminate inaccuracies caused by current changes during the voltage reference refresh.

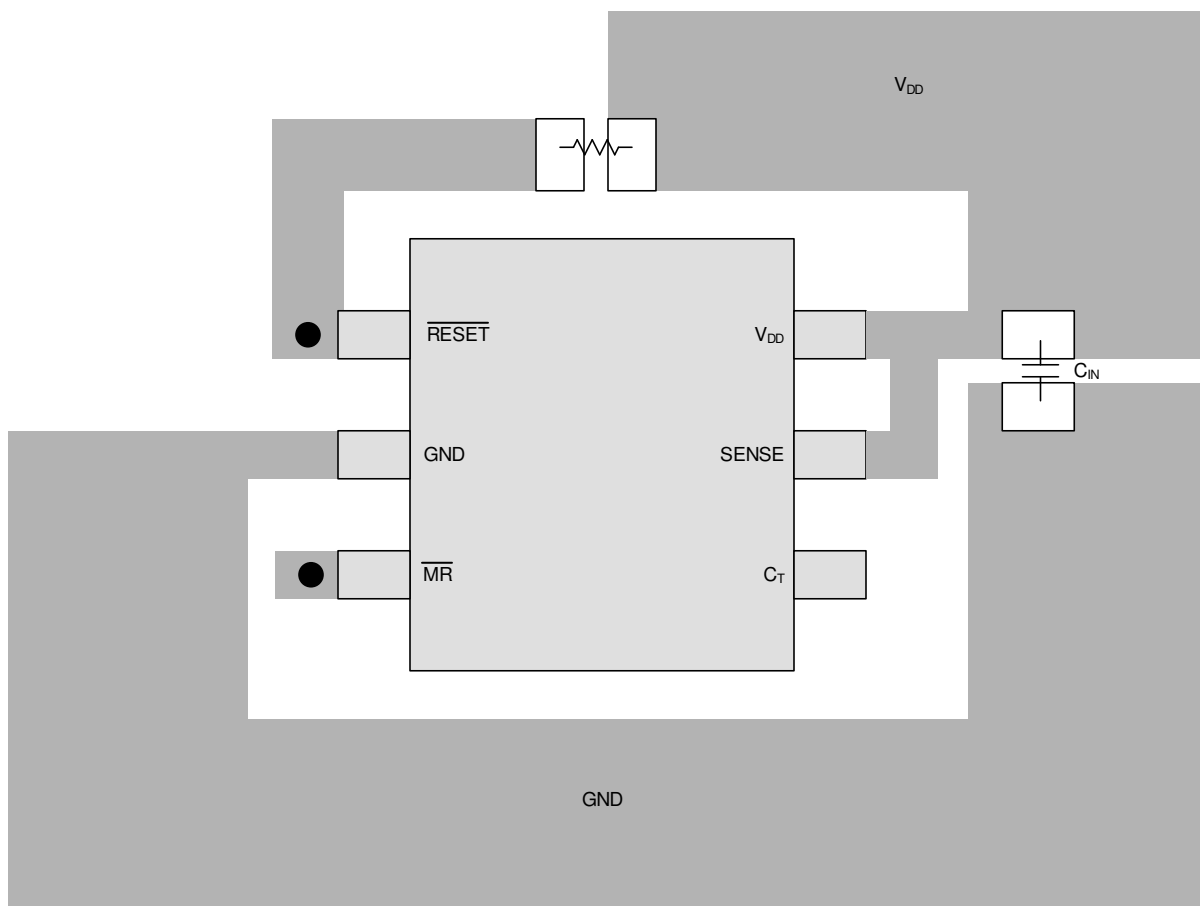
9.4 Layout

9.4.1 Layout Guidelines

Make sure the connection to the V_{DD} pin is low impedance. Place a 0.1- μF ceramic capacitor near the V_{DD} pin. If no capacitor is connected to the C_T pin, parasitic capacitance on this pin should be minimized so the RESET delay time is not adversely affected.

9.4.2 Layout Example

The layout example in [Figure 9-4](#) shows how the TPS3808E-Q1 is laid out on a printed circuit board (PCB) for a 20-ms delay.



● Vias used to connect pins for application-specific connections

Figure 9-4. Layout Example for a 20-ms Delay

10 Device and Documentation Support

10.1 Device Support

10.1.1 Development Support

10.1.1.1 Evaluation Modules

An evaluation module (EVM) is available to assist in the initial circuit performance evaluation using the TPS3808E-Q1. The [TPS3808EG01DBVEVM evaluation module](#) can be requested at the Texas Instruments website through the product folders or purchased directly from the [TI eStore](#) and is compatible with the TPS3808E-Q1. TPS3808E-Q1 sampled should be ordered and used to replace the existing TPS3808 device for testing.

10.2 Documentation Support

10.2.1 Related Documentation

The following related documents are available for download at www.ti.com:

- Application note. *Optimizing Resistor Dividers at a Comparator Input*. Literature number [SLVA450](#).
- Application note. *Sensitivity Analysis for Power Supply Design*. Literature number [SLVA481](#).
- TPS3808EG01DBVEVM Evaluation Module User Guide. Literature number [SBVU015](#).

10.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

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10.7 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

11 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (November 2023) to Revision B (December 2023)

Page

- | | |
|---------------------------------|---|
| • Remove TBD from EC table..... | 5 |
|---------------------------------|---|

Changes from Revision * (April 2023) to Revision A (November 2023)	Page
• 量産データのリリース.....	1

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most-current data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS3808EG01DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ01	Samples
TPS3808EG09DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ09	Samples
TPS3808EG125DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	Q125	Samples
TPS3808EG12DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ12	Samples
TPS3808EG15DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ15	Samples
TPS3808EG18DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(EG18, EQ18)	Samples
TPS3808EG19DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ19	Samples
TPS3808EG25DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ25	Samples
TPS3808EG30DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ30	Samples
TPS3808EG33DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ33	Samples
TPS3808EG50DBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	EQ50	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TPS3808E-Q1 :

- Catalog : [TPS3808E](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3808EG01DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG01DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG09DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG09DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG125DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG125DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG12DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG12DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG12DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG15DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG15DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG15DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG18DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG18DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG18DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG19DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG19DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG19DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG25DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG25DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3808EG30DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG33DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG33DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG50DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3808EG50DBVRQ1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS3808EG01DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG01DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG09DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG09DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG125DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG125DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG12DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG12DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG15DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG15DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG18DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG18DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG19DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG19DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG25DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG25DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG30DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG33DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS3808EG33DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG50DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS3808EG50DBVRQ1	SOT-23	DBV	6	3000	210.0	185.0	35.0

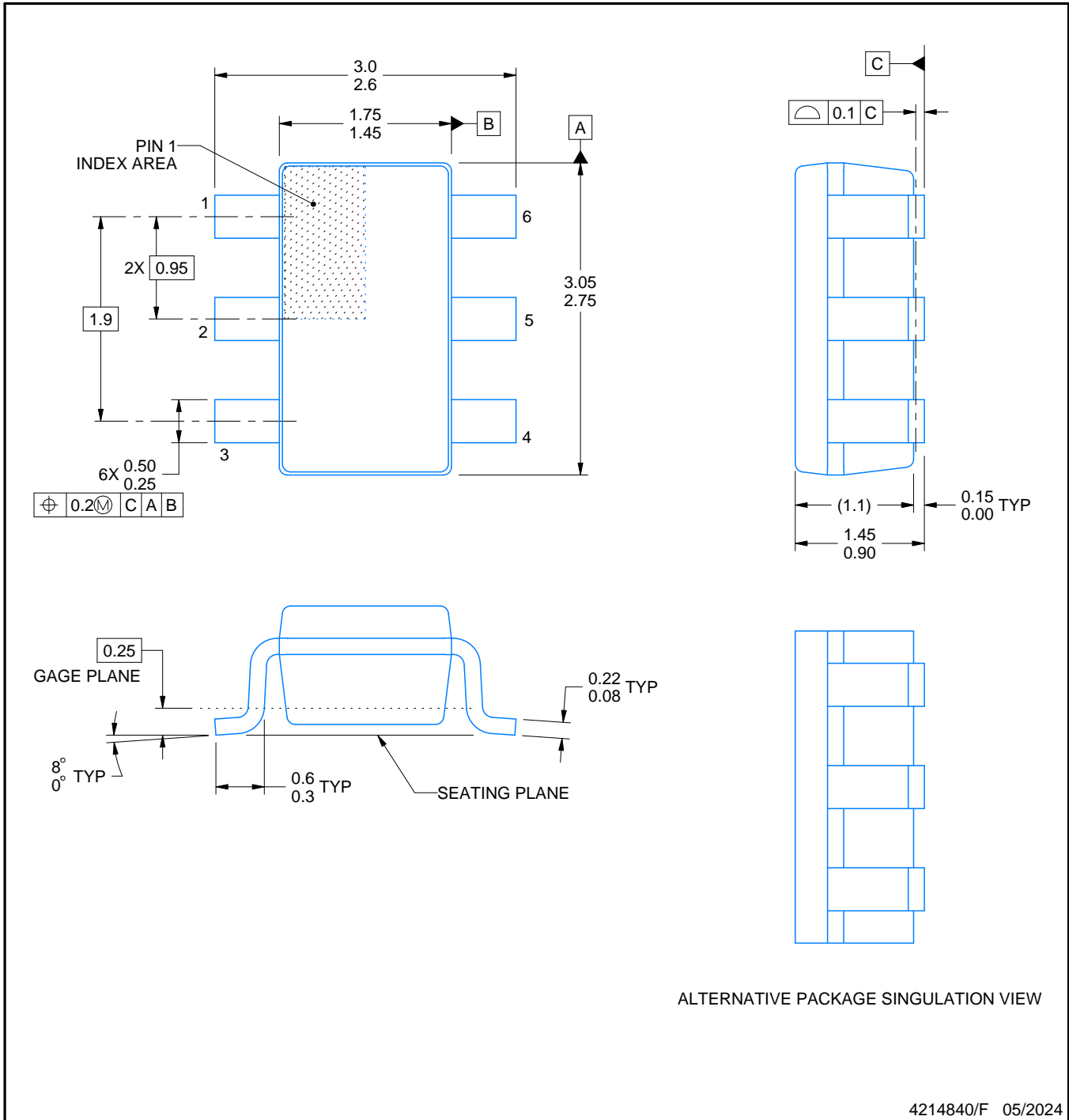
DBV0006A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



ALTERNATIVE PACKAGE SINGULATION VIEW

4214840/F 05/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Reference JEDEC MO-178.

EXAMPLE BOARD LAYOUT

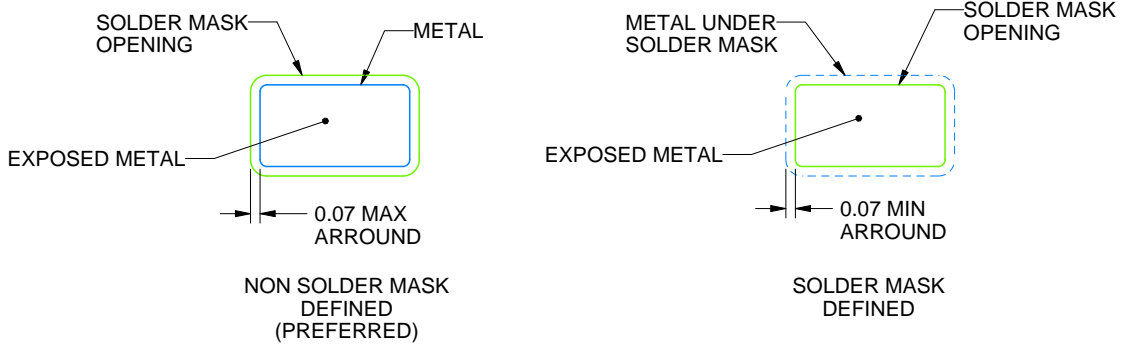
DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214840/F 05/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214840/F 05/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

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